



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220 Plastic-Encapsulate Transistors

KTD1351 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 3 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

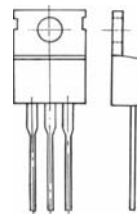
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-220

1. BASE

2. COLLECTOR

3. EMITTER



1 2 3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=50mA, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			100	μA
DC current gain	h_{FE}	$V_{CE}=5V, I_C=0.5A$	60		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{CE}=2A, I_B=0.2A$			1	V
Base-emitter voltage	V_{BE}	$V_{CE}=5V, I_C=0.5A$			1	V
Transition frequency	f_T	$V_{CE}=5V, I_C=0.5A$	2			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR
Range	60-120	100-200	150-300